DMG20402

Silicon NPN epitaxial planar type (Tr1) Silicon PNP epitaxial planar type (Tr2)

For general amplification

Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- \bullet Low collector-emitter saturation voltage $V_{CE(sat)}$
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

Marking Symbol: B7

Basic Part Number

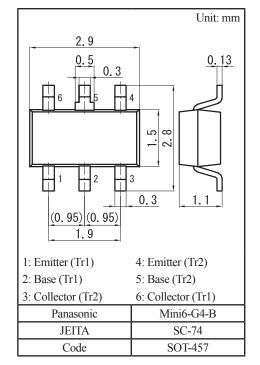
DSC2002 + DSA2002 (Individual)

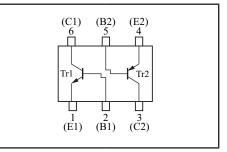
Packaging

DMG204020R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

	Parameter	Symbol	Rating	Unit
	Collector-base voltage (Emitter open)	V _{CBO}	60	V
Tr1	Collector-emitter voltage (Base open)	V _{CEO}	50	V
	Emitter-base voltage (Collector open)	V _{EBO}	5	V
	Collector current	I _C	500	mA
	Peak collector current	I _{CP}	1	А
	Collector-base voltage (Emitter open)	V _{CBO}	-60	V
Tr2	Collector-emitter voltage (Base open)	V _{CEO}	-50	V
	Emitter-base voltage (Collector open)	V _{EBO}	-5	V
	Collector current	I _C	-500	mA
	Peak collector current	I _{CP}	-1	А
	Total power dissipation	P _T	300	mW
Overall	Junction temperature	Tj	150	°C
	Storage temperature	T _{stg}	-55 to +150	°C





Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

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Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 {\rm mA}, I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	μΑ
Forward current transfer ratio ^{*1}	h _{FE1}	$V_{CE} = 10 \text{ V}, I_C = 150 \text{ mA}$	120		340	
Forward current transfer ratio	h _{FE2}	$V_{CE} = 10 \text{ V}, I_C = 500 \text{ mA}$	40			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_{\rm C} = 300 \text{ mA}, I_{\rm B} = 30 \text{ mA}$		0.1	0.6	V
Transition frequency	\mathbf{f}_{T}	$V_{CE} = 10 \text{ V}, I_C = 50 \text{ mA}$		160		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		4.8	15	pF

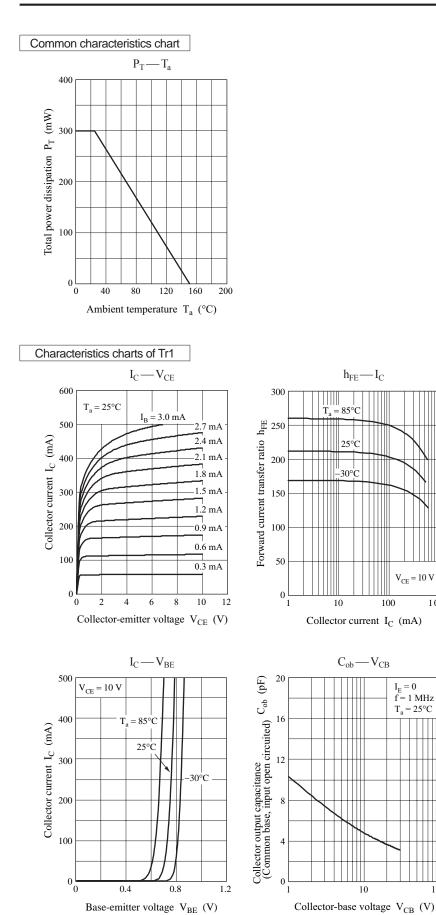
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

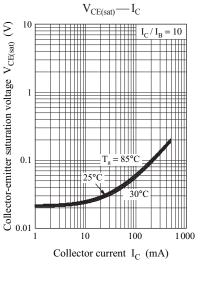
2. *1: Pulse measurement

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = -10 \ \mu \text{A}, I_{\rm C} = 0$	-5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Forward current transfer ratio *1	h _{FE1}	$V_{\rm CE} = -10$ V, $I_{\rm C} = -150$ mA	120		340	
Forward current transfer ratio	h _{FE1}	$V_{\rm CE} = -10$ V, $I_{\rm C} = -500$ mA	40			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_{\rm C} = -300 \text{ mA}, I_{\rm B} = -30 \text{ mA}$		- 0.2	- 0.6	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_{\rm C} = -300 \text{ mA}, I_{\rm B} = -30 \text{ mA}$		- 0.9	-1.5	V
Transition frequency	f _T	$V_{\rm CE} = -10$ V, $I_{\rm C} = -50$ mA		130		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10$ V, $I_E = 0$, $f = 1$ MHz		7.3	15	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

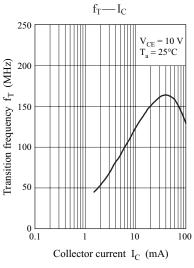
2. *1: Pulse measurement



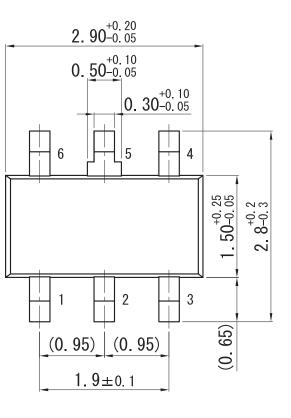


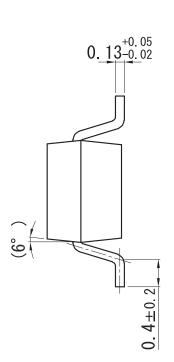
1000

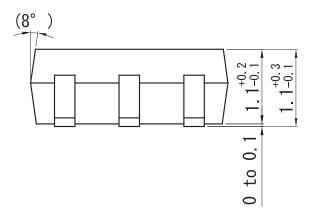
100



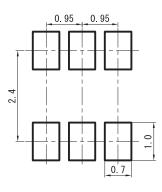
Mini6-G4-B







Land Pattern (Reference) (Unit: mm)



Ver. BED

Unit: mm

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